

## In the Claims

### CLAIMS

Claims 1-30 (Canceled).

31. (Previously presented) Integrated circuitry comprising:

a substrate;

a plurality of spaced conductive layers over the substrate and comprising upper surfaces;

a low-K material disposed over the substrate and between the conductive layers, an entirety of the low-K material being elevationally below the upper surfaces of the conductive layers; and

a dielectric material having a first portion disposed over the low-K material elevationally below and between the upper surfaces of the conductive layers and a second portion disposed over the upper surfaces of the conductive layers.

32. (Previously presented) The circuitry of claim 31 wherein the low-K material comprises a first low-K material and wherein the dielectric material comprises a second low-K material different from the first low-K material.

33. (Previously presented) The circuitry of claim 31 wherein the dielectric material comprises a hydrogen silsesquioxane material.

34. (Previously presented) The circuitry of claim 31 wherein the low-K material comprises a carbon-comprising silicon oxide material.

35. (Previously presented) The circuitry of claim 31 wherein the low-K material comprises a first low-K material and wherein the dielectric material comprises a second low-K material having the same composition as the first low-K material.

36. (Previously presented) The circuitry of claim 31 further comprising a barrier layer disposed between the low-K material and the dielectric material.

37. (Previously presented) The circuitry of claim 31 further comprising two barrier layers disposed between the low-K material and the dielectric material.

38. (Previously presented) The circuitry of claim 31 further comprising at least two barrier layers disposed between the spaced conductive layers.

39. (Previously presented) The circuitry of claim 31 further comprising a barrier layer disposed between the upper surfaces of the spaced conductive layers and the dielectric material.

40. (Previously presented) The circuitry of claim 31 further comprising a barrier layer having a first portion disposed between the upper surfaces of the spaced conductive layers and the dielectric material and a second portion disposed between the low-K material and the dielectric material.

Claims 41-50 (Canceled).